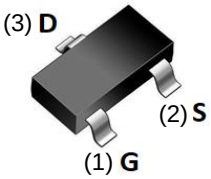
WG3N04

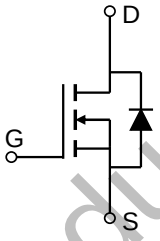
Features:

- ☐ Advanced Trench Technology
- ☐ Excellent Switching Characteristics
- ☐ Extended Safe Operating Area
- ☐ Ultra Low Gate Charge:Qg=10nC (Typ.)
- ☐ VDSS=40V, ID=5A
- ☐ Rds(on): 33mΩ(Typ.) @VG=10V
- ☐ 100% Avalanche Tested

SOT-23

RoHS COMPLIANT





Schematic diagram

1:Gate (G)
2:Source (S)
3:Drain (D)

MARKING: 3N04A

Absolute Maximum Ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol		Value	Unit
Drain-Source Voltage	V_{DSS}		40	V
Drain Current	I_D	Tj=25℃	5	A
		Tj=100℃	2	
Gate-Source Voltage	V_{GSS}		±20	V
Pulsed Drain Current	I_{DM}		15	A
Power Dissipation (Tj=25℃)	P_D		1.3	W
Junction Temperature(Max)	T_j		150	℃
Storage Temperature	T_{stg}		-55~+150	℃
Maximum lead temperature for soldering purpose,1/8'from case for 5 seconds	TL		300	℃

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance,Junction to Case	$R_{\theta JC}$	-	-	℃/W
Thermal Resistance,Junction to Ambient	$R_{\theta JA}$	-	-	℃/W

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 40V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.9	2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 3A	-	33	39	mΩ
		V_{GS} = 4.5V, I_D = 3A	-	40	52	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz	-	536	-	pF
C_{oss}	Output Capacitance		-	42	-	pF
C_{rss}	Reverse Transfer Capacitance		-	33	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DD} = 20V, I_D = 3A	-	10	-	nC
Q_{gs}	Gate Source Charge		-	2	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 20V I_D= 3A, R_{GEN} = 3Ω	-	4	-	ns
t_r	Turn-On Rise Time		-	2	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	15	-	ns
t_f	Turn-Off Fall Time		-	2	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 5A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 3A, di/dt = 100A/us	-	9	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	4	-	nC

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Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Output Characteristics

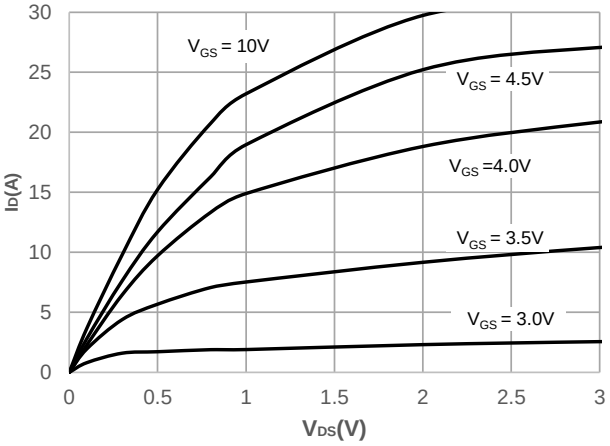


Figure 2: Typical Transfer Characteristics

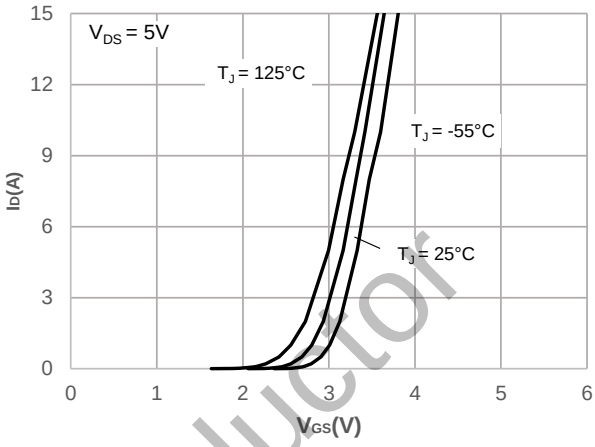


Figure 3: On-resistance vs. Drain Current

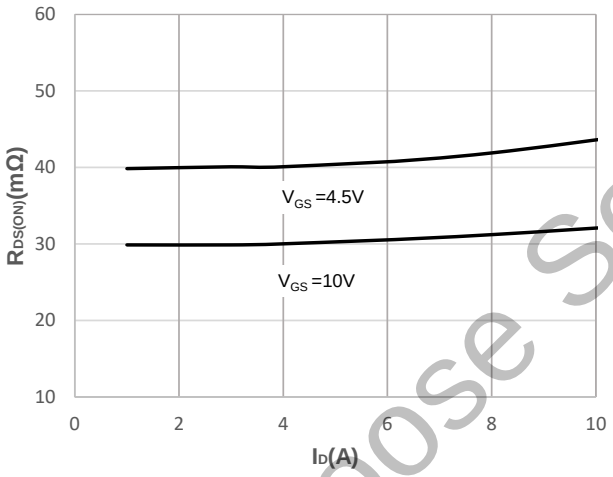


Figure 4: Body Diode Characteristics

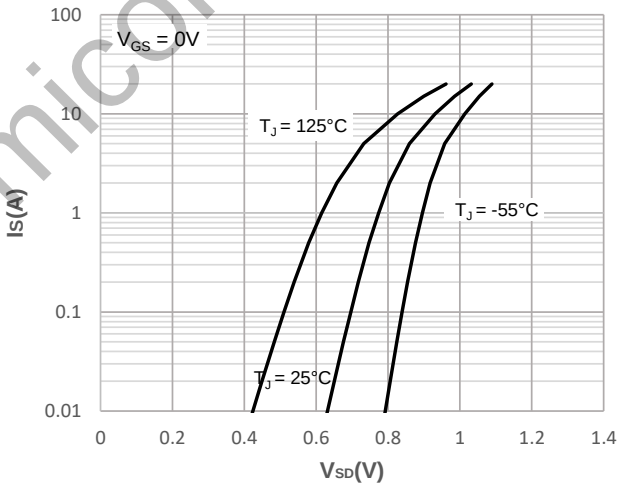


Figure 5: Gate Charge Characteristics

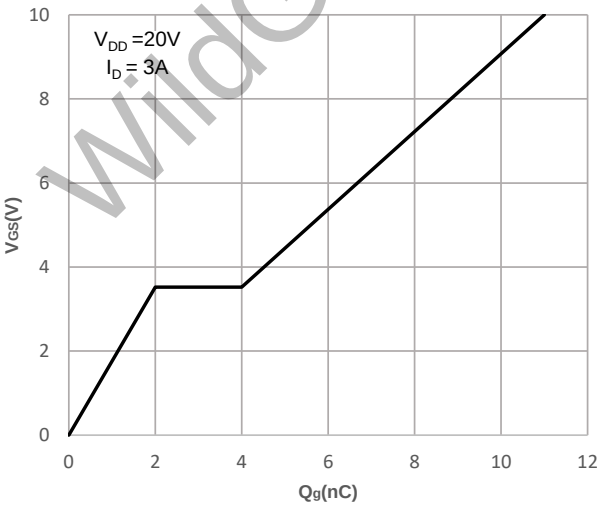
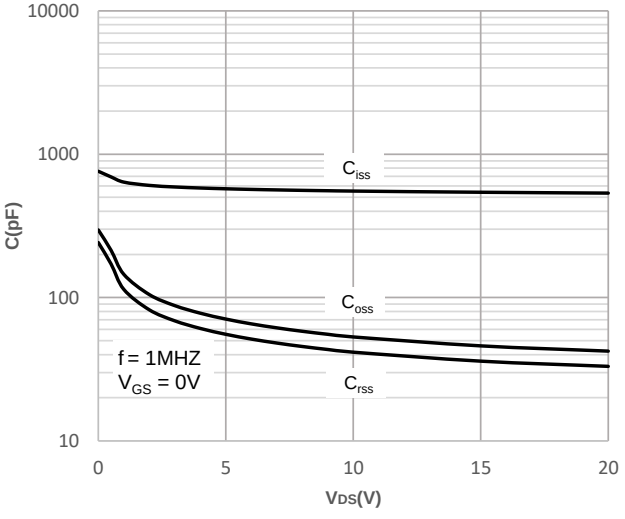


Figure 6: Capacitance Characteristics



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Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

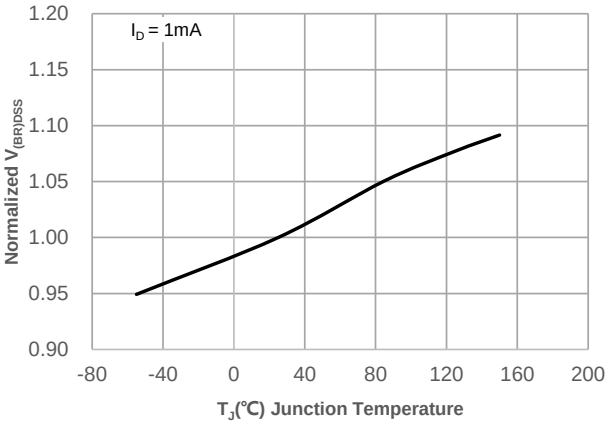


Figure 8: Normalized on Resistance vs. Junction Temperature

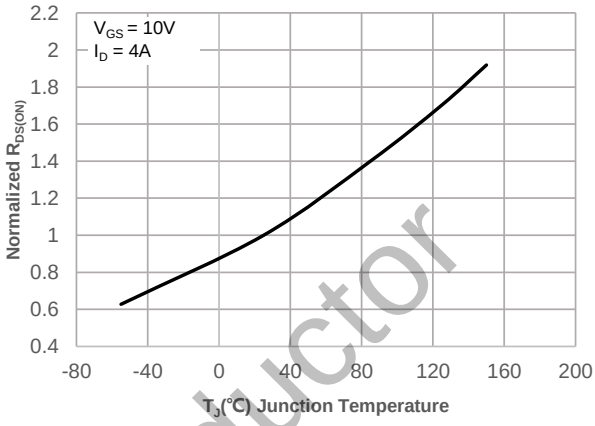


Figure 9: Maximum Safe Operating Area

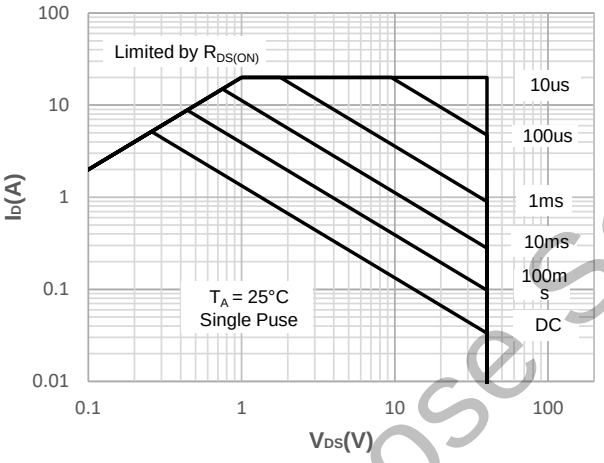


Figure 10: Maximum Continuous Drian Current vs. Ambient Temperature

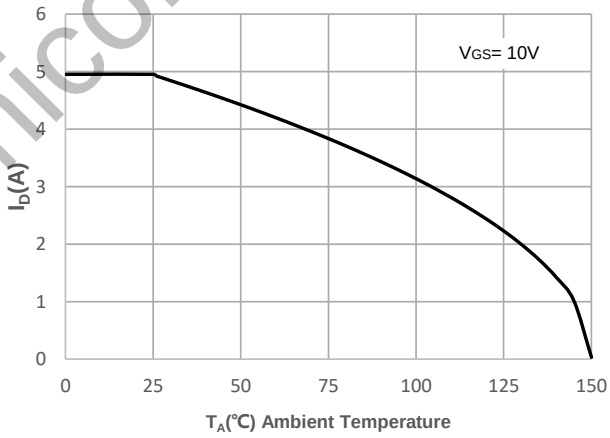


Figure 11: Normalized Maximum Transient Thermal Impedance

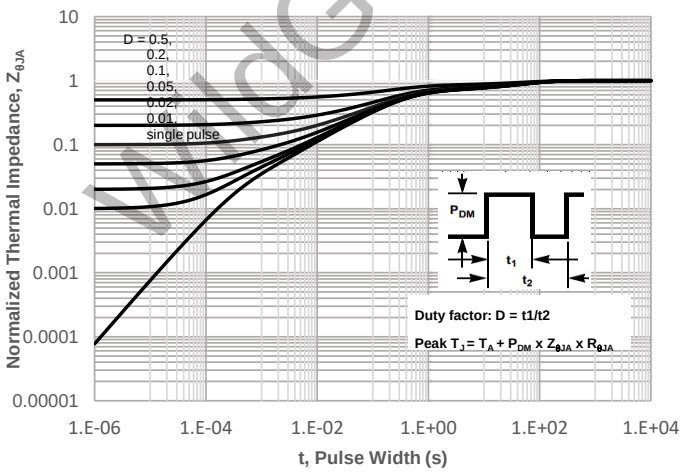
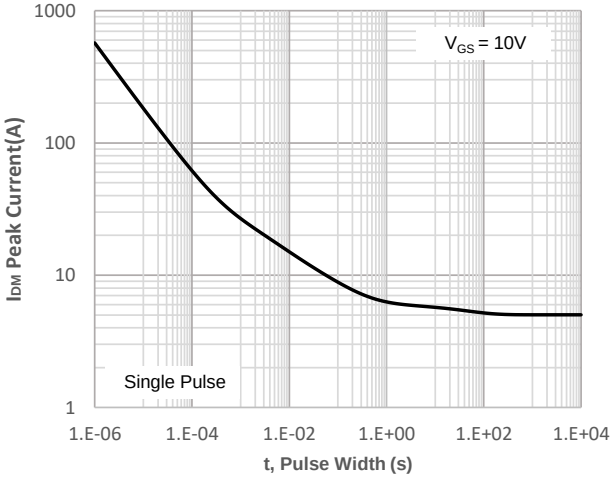


Figure 12: Peak Current Capacity



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Test Circuit

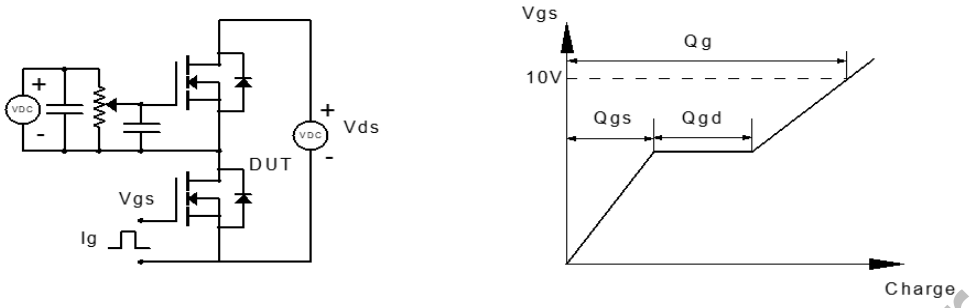


Figure 1: Gate Charge Test Circuit & Waveform

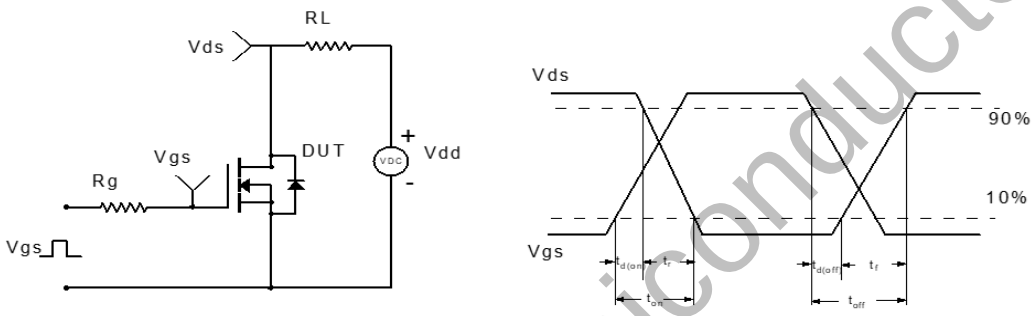


Figure 2: Resistive Switching Test Circuit & Waveform

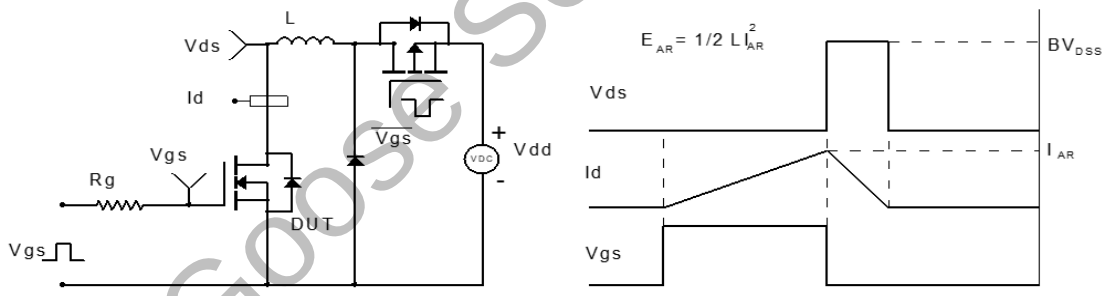


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

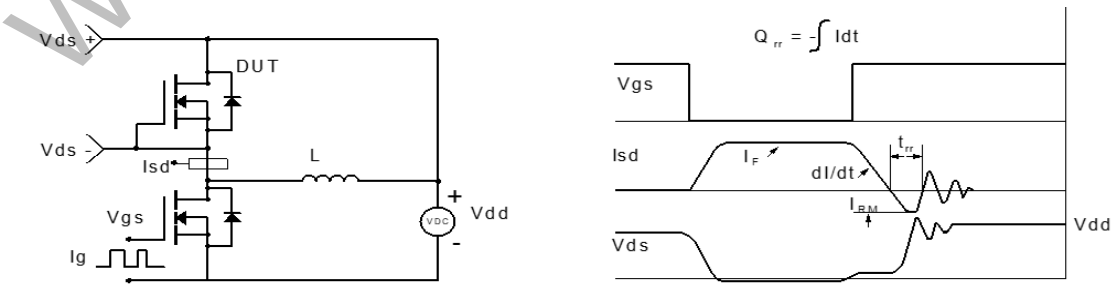


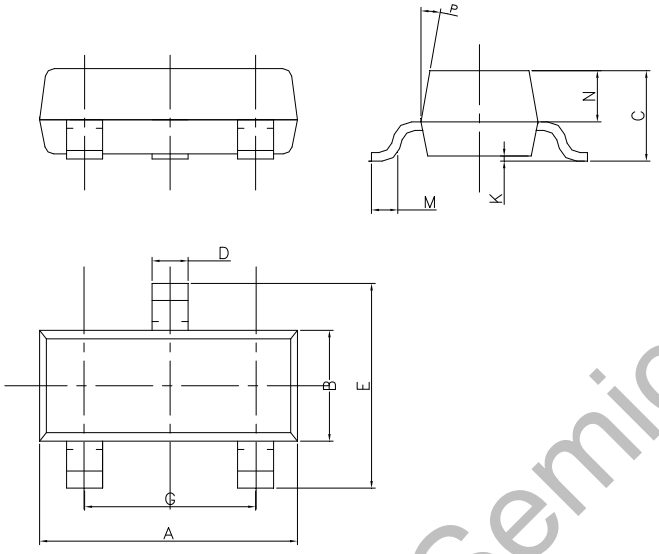
Figure 4: Diode Recovery Test Circuit & Waveform

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Package Dimension

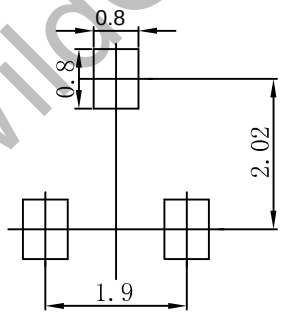
SOT-23

Unit: mm



DIM	MILLIMETERS
A	2.85~3.04
B	1.30±0.10
C	1.00±0.10
D	0.45±0.05
E	2.25~2.55
G	1.90±0.1
K	0.00−0.10
M	0.20 MIN
N	0.60±0.10
P	7±2°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

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